

Numerical Analysis of Asymmetric Differential Inductors

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Background

Matrix-Decomposition Technique

Simulation & Measurement Results

Summary

Miniaturization of CMOS process

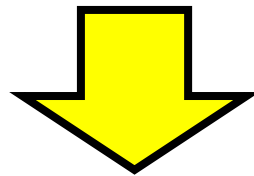
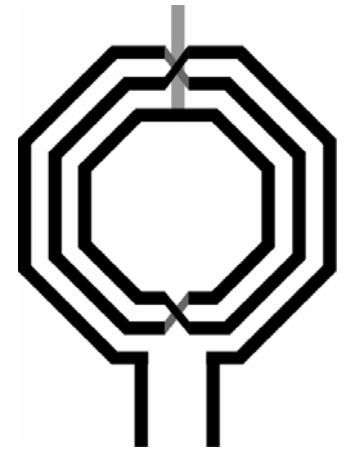
Difficulty of characterize on-chip inductors

Degradation of circuit performances

On-chip differential inductor

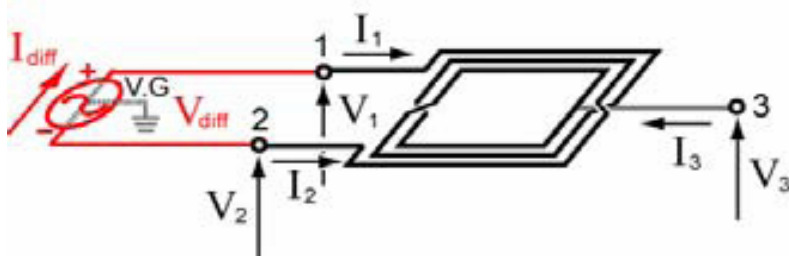
Used for LC-VCO, differential LNA, Mixer...

Mismatch between left and right halves degrades circuit performances.



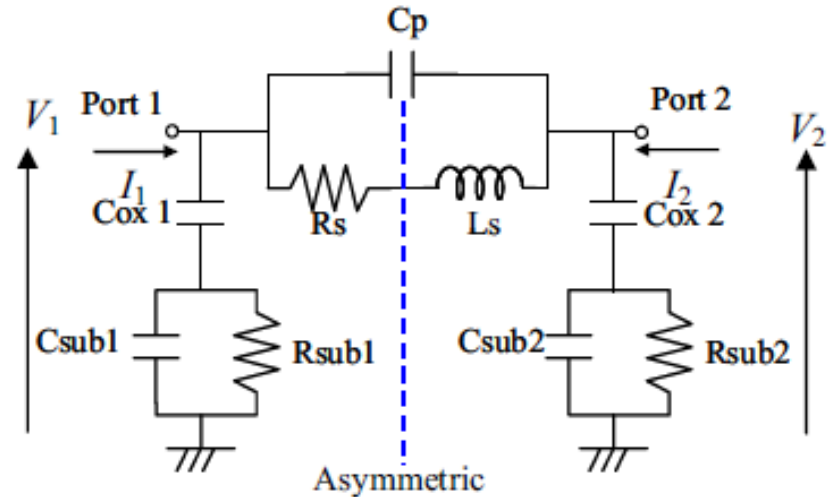
Accurate modeling of on-chip symmetric inductor
Extract of asymmetric parameters

- 3-port symmetric inductor analysis in various operation modes [1]
 - Circuit parameters are extracted by numerical optimization
 - Symmetry is assumed in the parameters
- Asymmetric properties are estimated from Y11 and Y22 [2]
 - The difference is involved in only difference in shunt parasitic components



$$Z_{\text{diff}} = \frac{V_{\text{diff}}}{I_{\text{diff}}} = \frac{2(Y_{23} + Y_{13})}{Y_{23}(Y_{11} - Y_{12}) - Y_{13}(Y_{21} - Y_{22})}$$

$$\therefore L_{\text{diff}} = \frac{1}{\omega} \text{Im}(Z_{\text{diff}}) \quad Q_{\text{diff}} = \frac{\text{Im}(Z_{\text{diff}})}{\text{Re}(Z_{\text{diff}})}$$

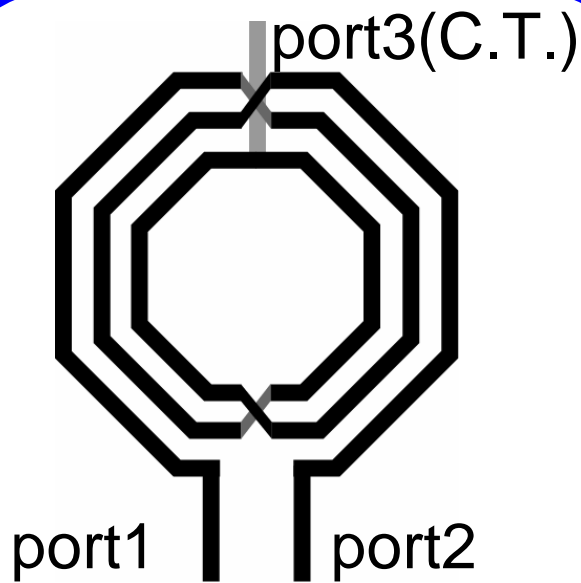


[1] K. Okada, *et al.*, EuMC, Oct. 2007, pp. 520– 523.

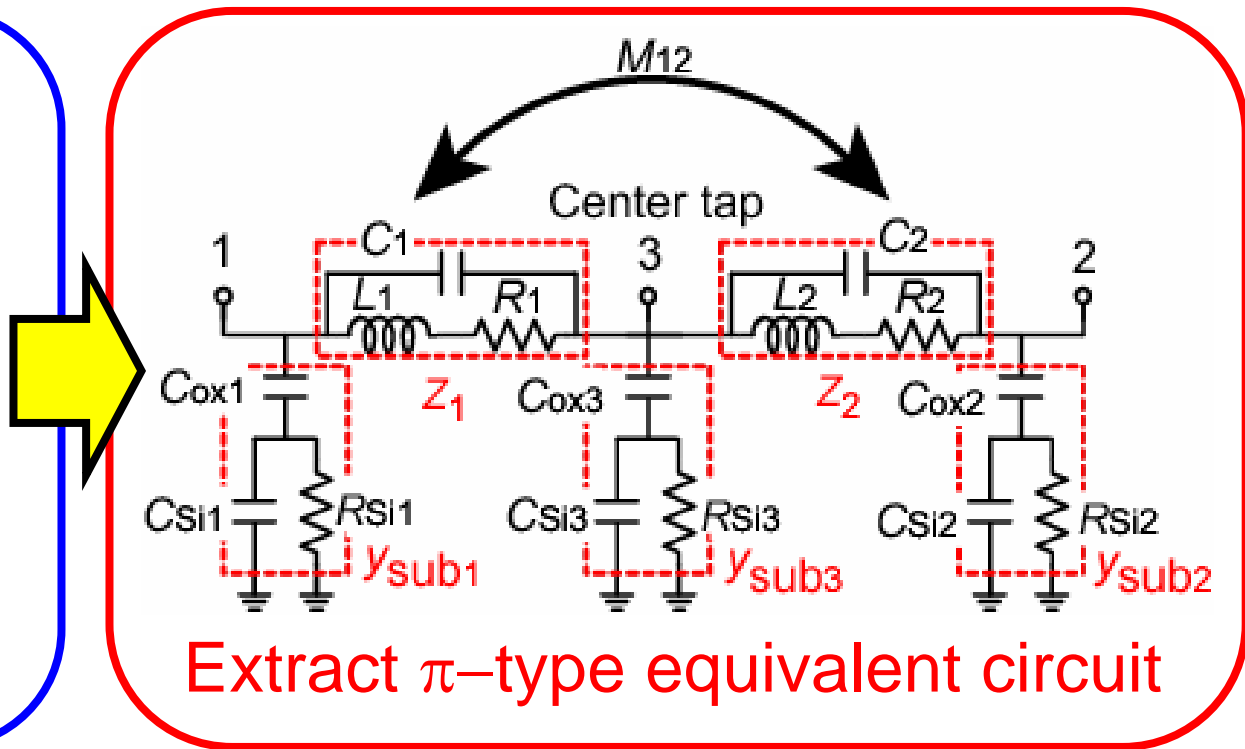
[2] Y. Aoki, *et al.*, EuMC, Oct. 2007, pp. 339–342.

Proposed method

by Matrix-Decomposition Technique



3port S-parameter



- Physically reliable parameters can be extracted.
- The mismatch can be accurately evaluated.

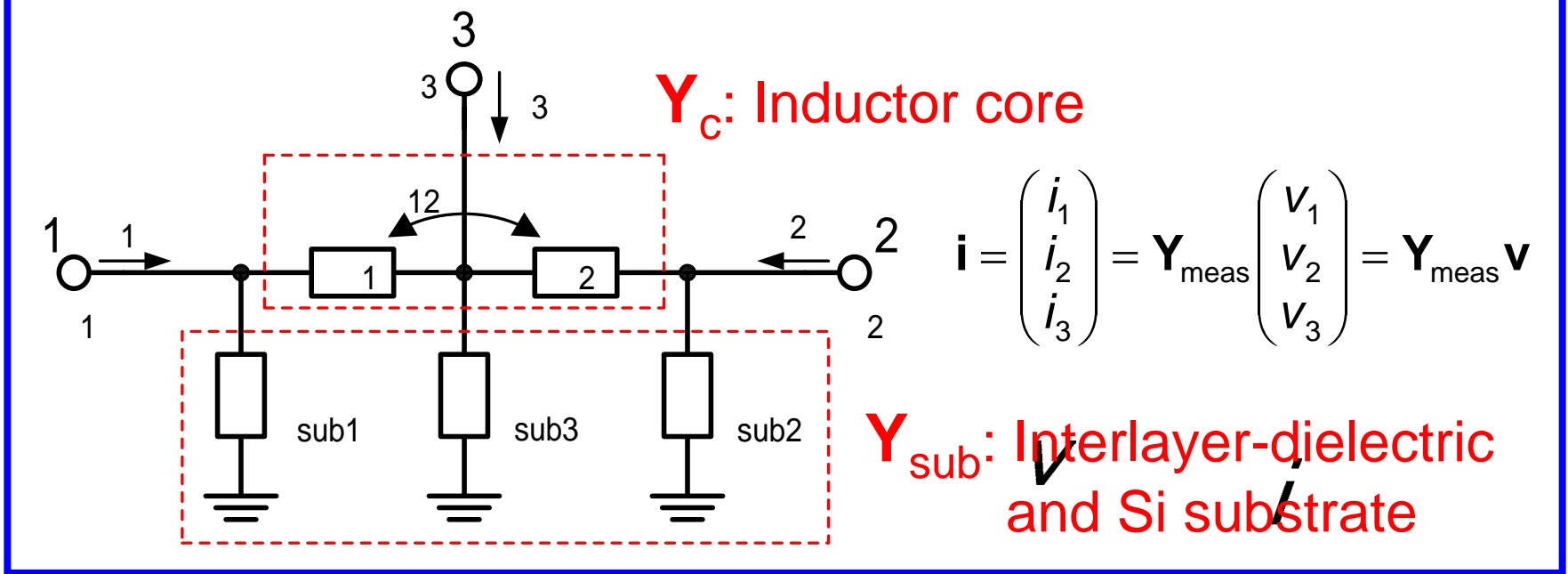
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Matrix-Decomposition Technique

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$$Y_{\text{meas}} = Y_c + Y_{\text{sub}}$$



All ports have common voltages

Y_c can be ignored Y_{sub} is calculated from Y_{meas}

Y_c is calculated from Y_{meas} and Y_{sub}

Z_{core} is derived from Y_c by converting matrix

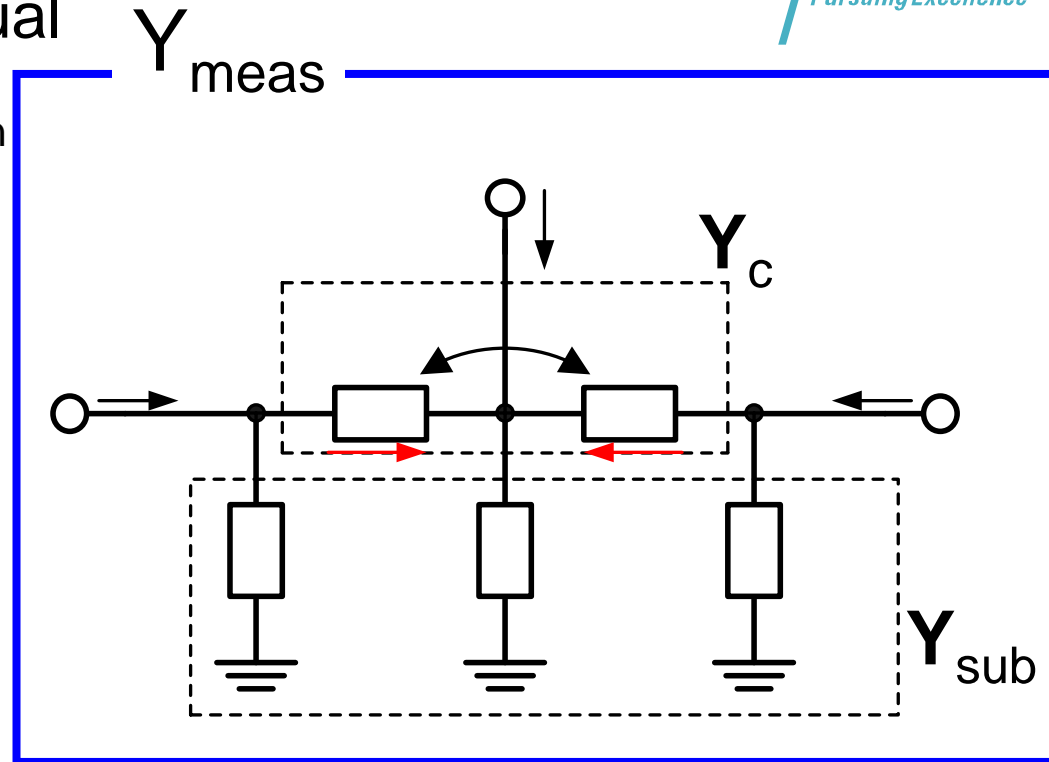
Calculation of Y_{sub}

Voltages of each port are equal

No current flows through z_n

$$\begin{pmatrix} i_1 \\ i_2 \\ i_3 \end{pmatrix} = \mathbf{Y}_{\text{meas}} \begin{pmatrix} V_a \\ V_a \\ V_a \end{pmatrix}$$

$$= \mathbf{Y}_c \begin{pmatrix} V_a \\ V_a \\ V_a \end{pmatrix} + \mathbf{Y}_{\text{sub}} \begin{pmatrix} V_a \\ V_a \\ V_a \end{pmatrix} = 0$$



$$\mathbf{Y}_{\text{sub}} = \begin{pmatrix} y_{\text{sub}1} & 0 & 0 \\ 0 & y_{\text{sub}2} & 0 \\ 0 & 0 & y_{\text{sub}3} \end{pmatrix}$$

$$y_{\text{sub}1} = y_{\text{meas}11} + y_{\text{meas}12} + y_{\text{meas}13}$$

$$y_{\text{sub}2} = y_{\text{meas}21} + y_{\text{meas}22} + y_{\text{meas}23}$$

$$y_{\text{sub}3} = y_{\text{meas}31} + y_{\text{meas}32} + y_{\text{meas}33}$$

Conversion of matrix Y_c to Z_{core}

$$Y_c = Y_{meas'} - Y_{sub}$$

Define Z_{core} by 2×2 matrix

$$Z_{core} = \begin{pmatrix} z_1 & -j\omega M_{12} \\ -j\omega M_{12} & z_2 \end{pmatrix} \quad v_z = Z_{core} i_z$$

$$v_z = Av \quad i_z = Bi$$

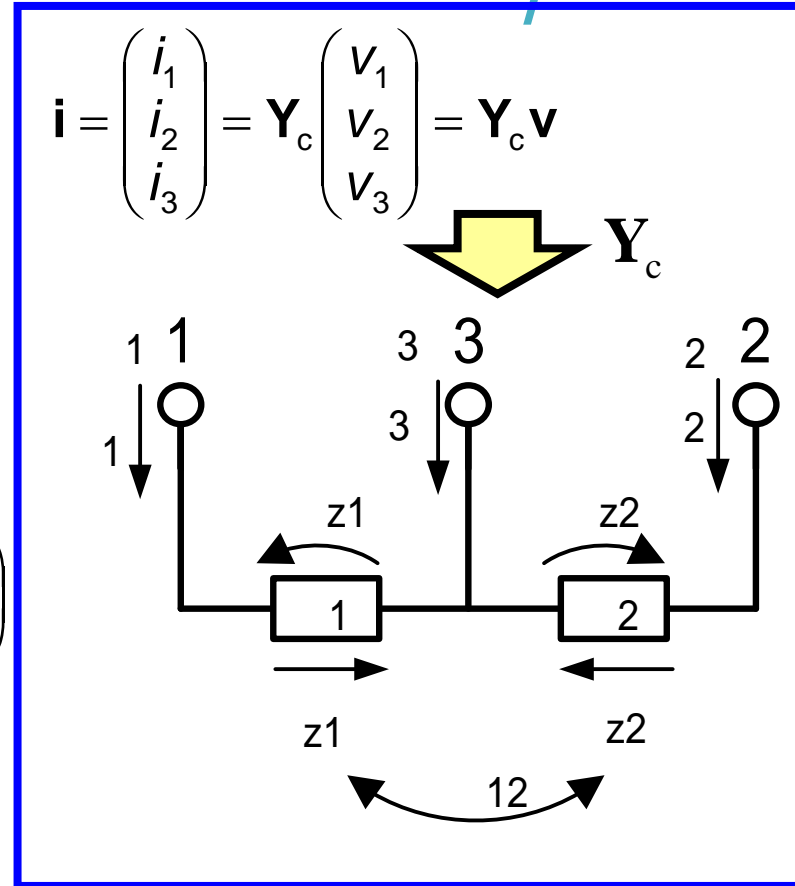
Obtain converting matrix **A** and **B**

$$B^T \text{ can be } A^* \quad AA^* = I$$

e.g.) $v_z = \begin{pmatrix} v_{z1} \\ v_{z2} \end{pmatrix} = \begin{pmatrix} v_1 - v_3 \\ v_2 - v_3 \end{pmatrix} \quad i_z = \begin{pmatrix} i_{z1} \\ i_{z2} \end{pmatrix} = \begin{pmatrix} i_1 \\ i_2 \end{pmatrix}$

$$A = \begin{pmatrix} 1 & 0 & -1 \\ 0 & 1 & -1 \end{pmatrix} \quad B = \begin{pmatrix} 1 & 0 & 0 \\ 0 & 1 & 0 \end{pmatrix}$$

Matrix Y_c is converted into matrix Z_{core}



$$Av = Z_{core} Bi = Z_{core} B Y_c v \quad \Rightarrow \quad Z_{core} = (B Y_c A^*)^{-1}$$

$$A = Z_{core} B Y_c$$

Background

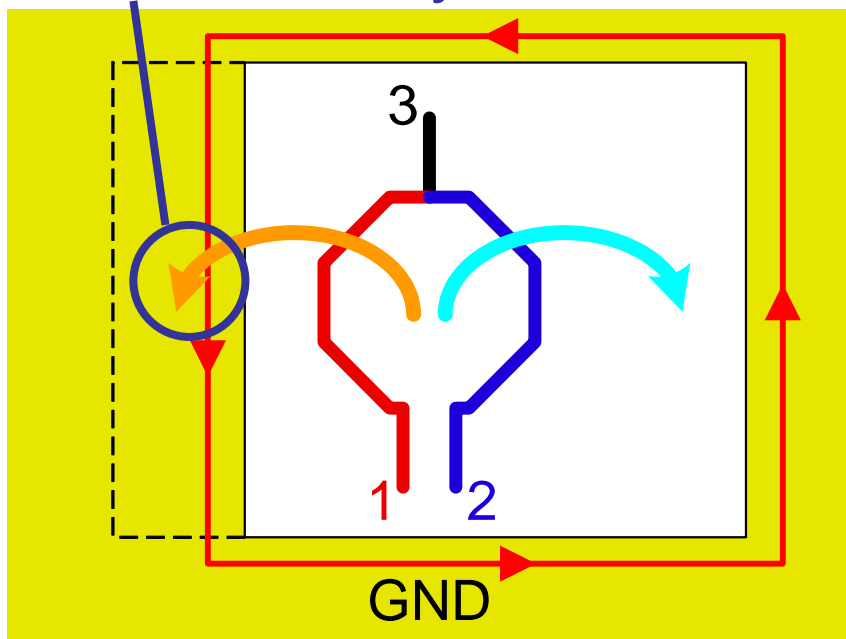
Matrix-Decomposition Technique

Simulation & Measurement Results

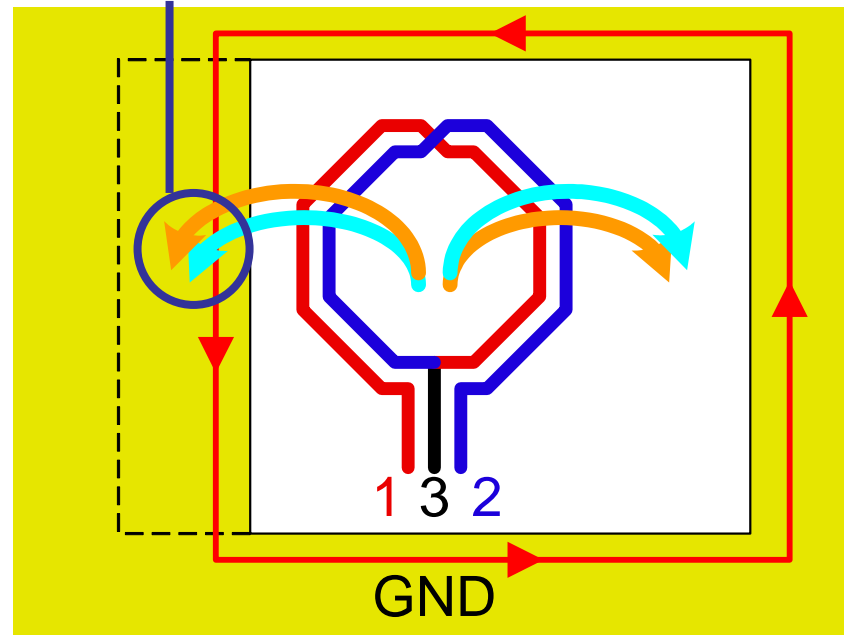
Summary

Mismatch of ground loop

Flux loss: Only half side



Flux loss: Both sides

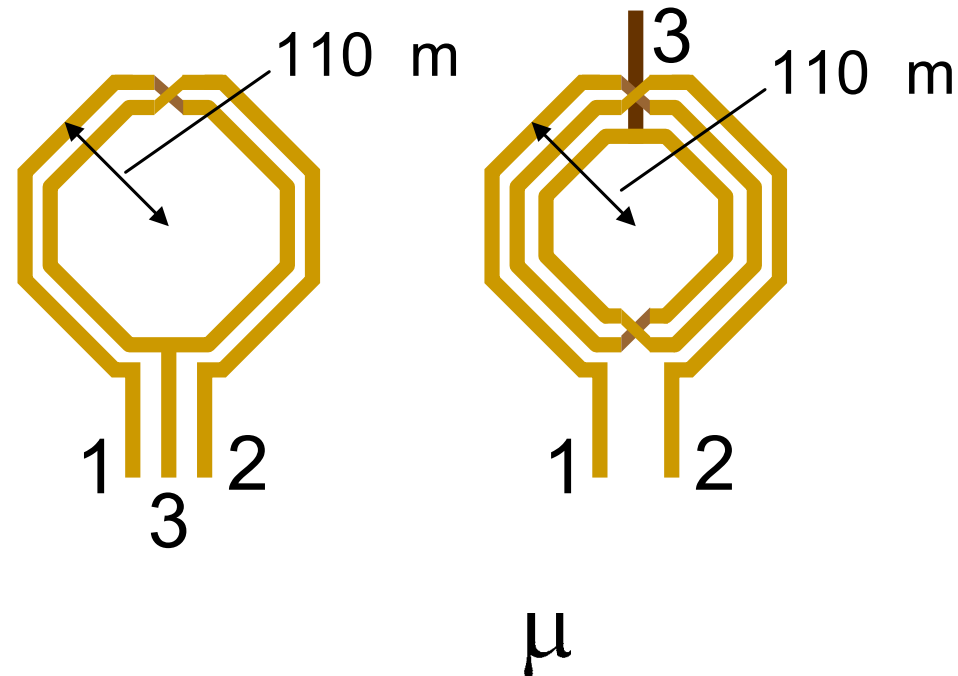
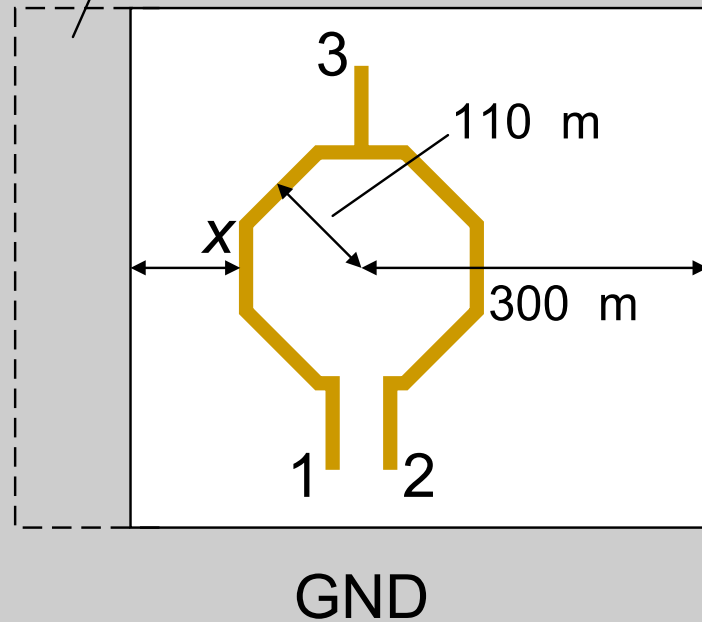


The inductance mismatch depends on the number of turns.

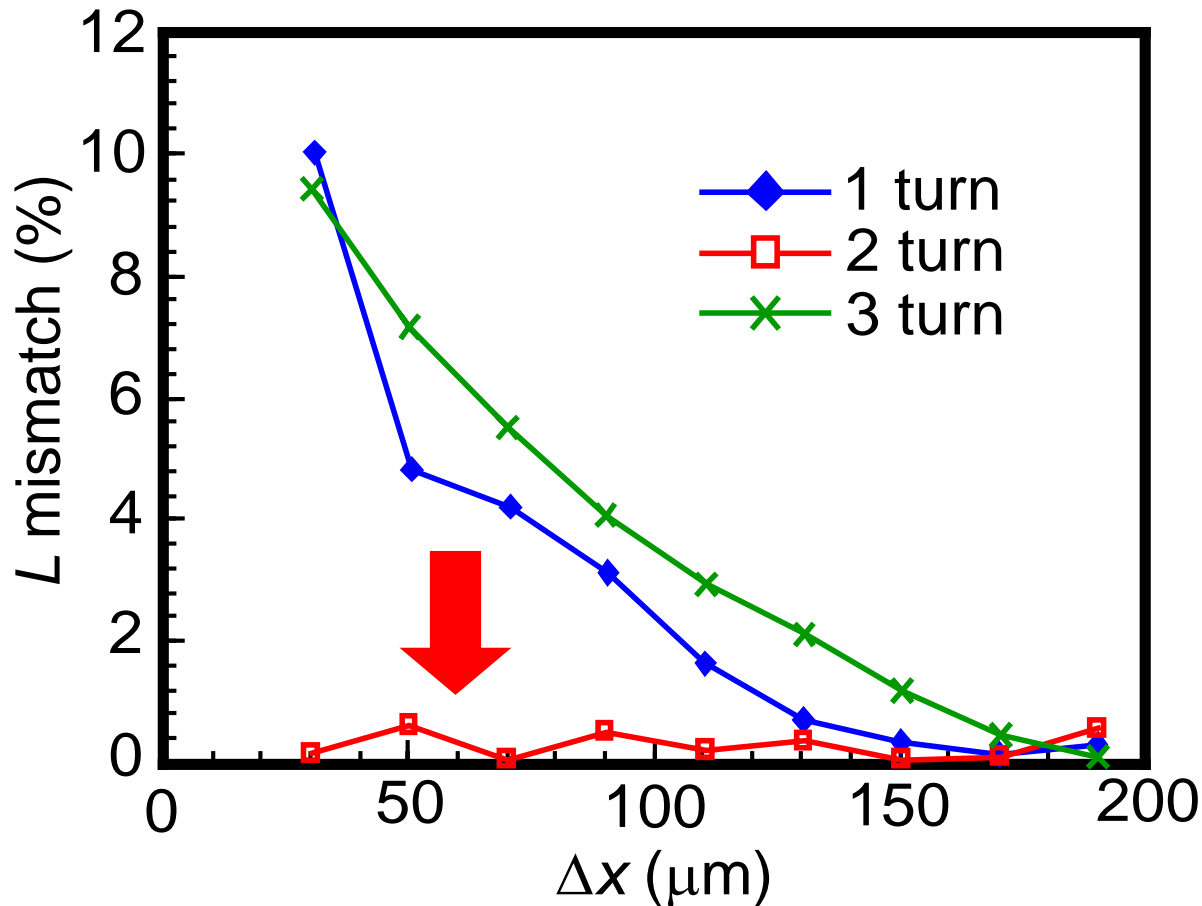
Odd \Rightarrow Each loss is different \Rightarrow Mismatch

Even \Rightarrow Each loss is almost equal \Rightarrow Mismatch

dummy GND



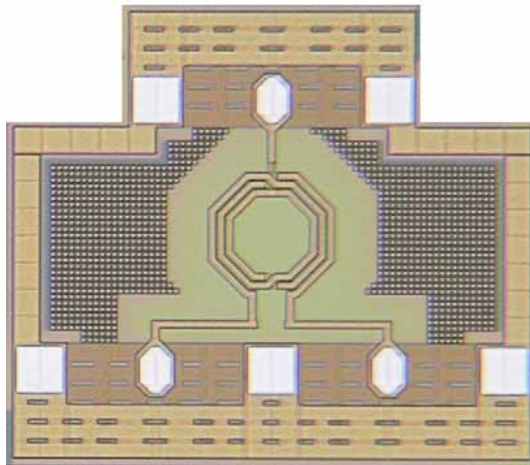
- Inductance mismatches are evaluated by the proposed method.
- The mismatches are plotted as a function of Δx .



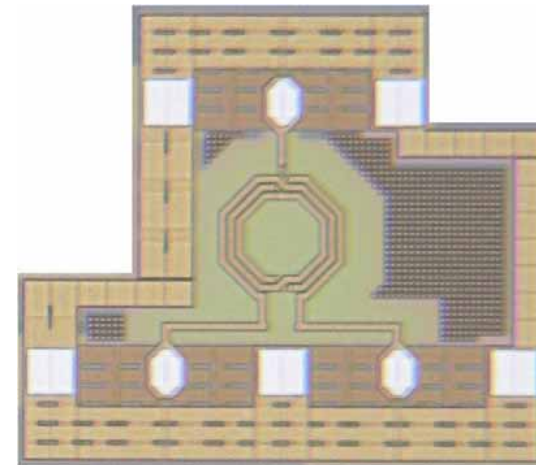
- The mismatch of 2-turn is smaller than 1- and 3-turn
- Increasing Δx , mismatch decreases

0.18 μm Si-CMOS

Line width : $9\mu\text{m}$, Line space : $2\mu\text{m}$
Inner diameter : $100\mu\text{m}$, Turn : 3



Symmetric



Asymmetric

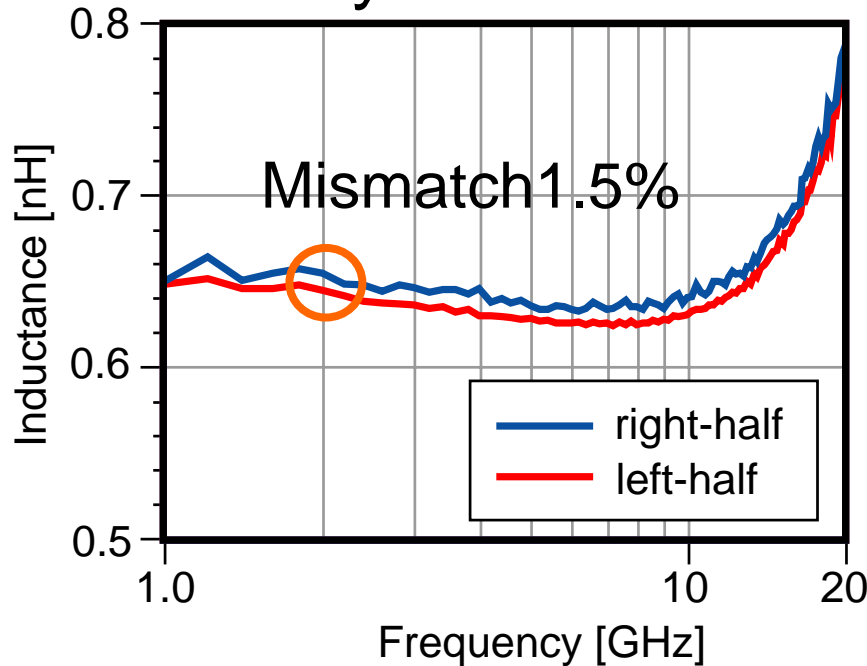
VNA : 4port 10MHz-67GHz

E8361A+N4421BH67(Agilent)

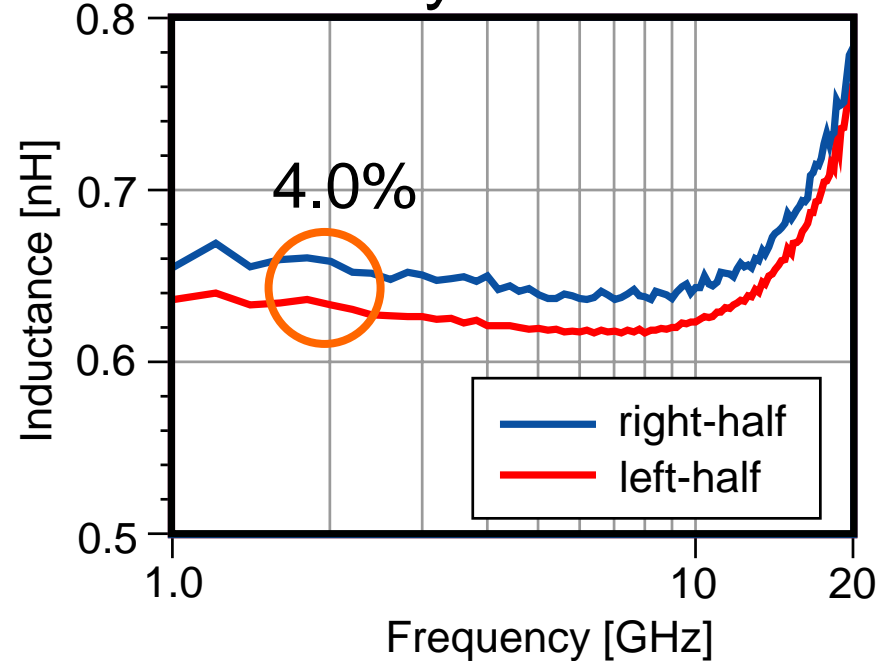
Probe : I67-D-GSGSG-150 (Cascade)

I67-GSG-150 (Cascade)

Symmetric



Asymmetric



- Influence of asymmetric ground loop is extracted
- Other reasons to cause asymmetry exist

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The numerical analysis using the matrix-decomposition technique is proposed

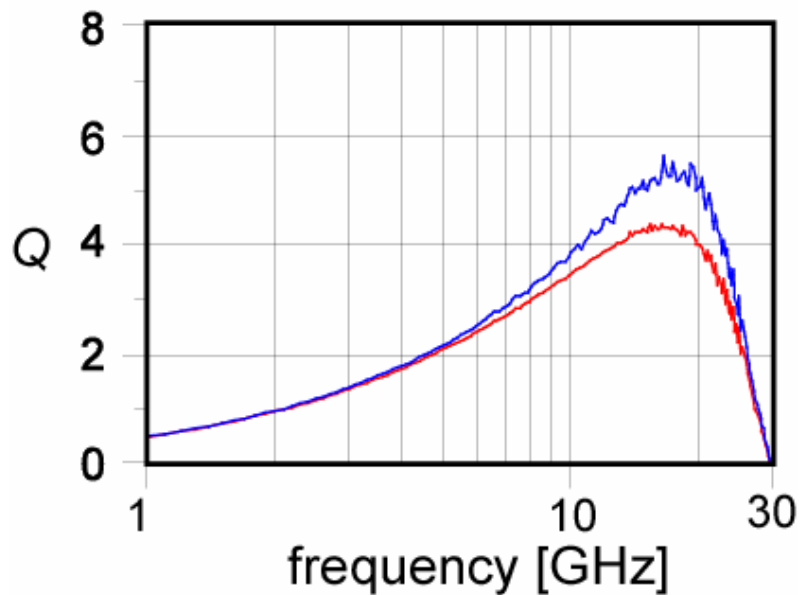


- Physically reliable parameter can be extracted
- The mismatch can be accurately evaluated

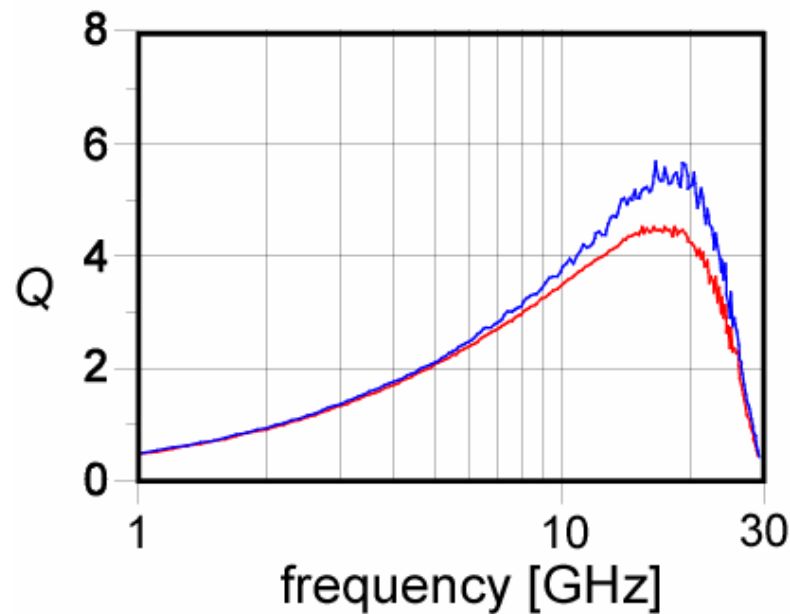
Proposed method is applied to 1-, 2-, and 3-turn differential inductors



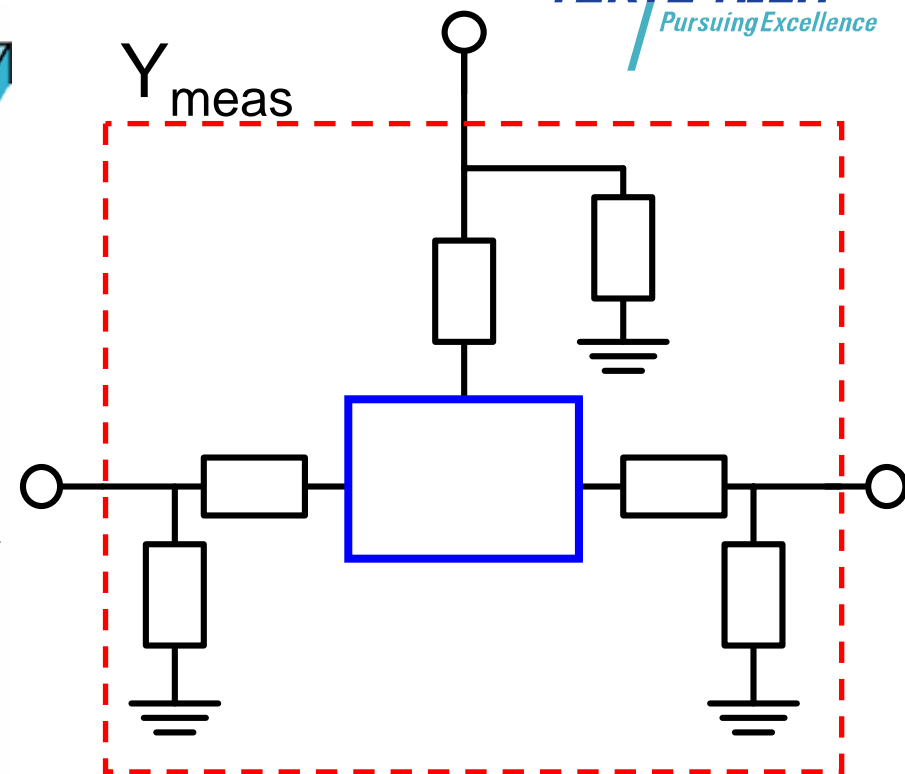
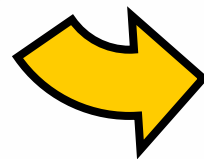
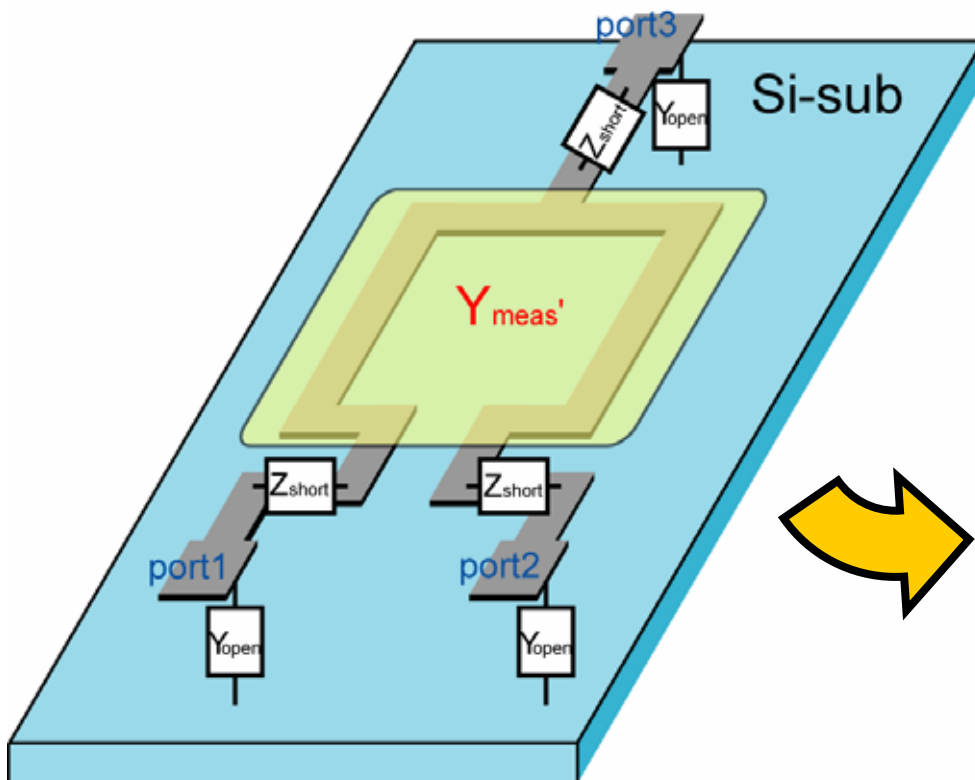
Influence of asymmetric ground loop can be accurately extracted



Symmetric



Asymmetric



• Z_{short} and Y_{open} are removed by Open-Short de-embedding

$$\mathbf{Z}_{meas}' = (\mathbf{Y}_{meas} - \mathbf{Y}_{open})^{-1} - (\mathbf{Z}_{short} - \mathbf{Y}_{open})^{-1}$$

$$\mathbf{Y}_{meas}' = \mathbf{Z}_{meas}'^{-1}$$